

PDF DATA SHEET

EFORCEAUSTRALIA PTY.LTD ACN:159 503 401

MDL-III-808L/1~100mW

INFRARED DIODE LASER AT 808nm

Diode infrared laser module at 808nm is made features of ultra compact, long lifetime, low cost and easy operating, which is used in measurement, communication, spectrum analysis, etc.





SPECIFICATIONS

Wavelength (nm)	808±3			
Output power (mW)	>1, 10, 20, 30,, 100			
Transverse mode	Near TEM ₀₀			
Operating mode	CW			
Power stability (rms, over 4 hours)	<1%, <3%, <5%			
Warm-up time (minutes)	<5			
Beam divergence, full angle (mrad)	<1.0			
Dimensions of beam at the aperture (mm)	~4.0			
Beam height from base plate (mm)	24. 8			
Polarization ratio	>50:1			
Pointing stability after warm-up (mrad)	<0.05			
Operating temperature (°C)	10~35			
Power supply (90-264VAC or 5VDC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM	
Modulation option	TTL/Analog 1Hz-	TTL/Analog 1Hz-5KHz, 1Hz-10KHz, 1Hz-30KHz, and TTL on/off		
Expected lifetime (hours)	10000	10000		
Warranty	1 year	1 year		





